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U.S. PATENT DOCUMENTS

OTHER DOCUMENTS

AICS	article entitled, "Polycrystalline silicon thin films formed by metal-induced solid phase crystallization of amorphous silicon", Y. Z. Wang et al., J. Vac. Sci. Technol. A, Vol. 16, No. 6, 1998, pp. 3352-3358.
AICS	article entitled, "Spectroscopic ellipsometry investigation of nickel silicide formation by rapid thermal process", Y. Hu et al., J. Vac. Sci. Technol. A, Vol. 16, No. 3, 1998, pp. 1820-1824.
AICS	article entitled, "Low Temperature Poly-Si Thin-Film Transistor Fabrication by Metal-Induced Lateral Crystallization", S-W Lee et al. IEEE Electron Device Letters, Vol. 17, No. 4, 1996, pp. 160-162.

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